

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

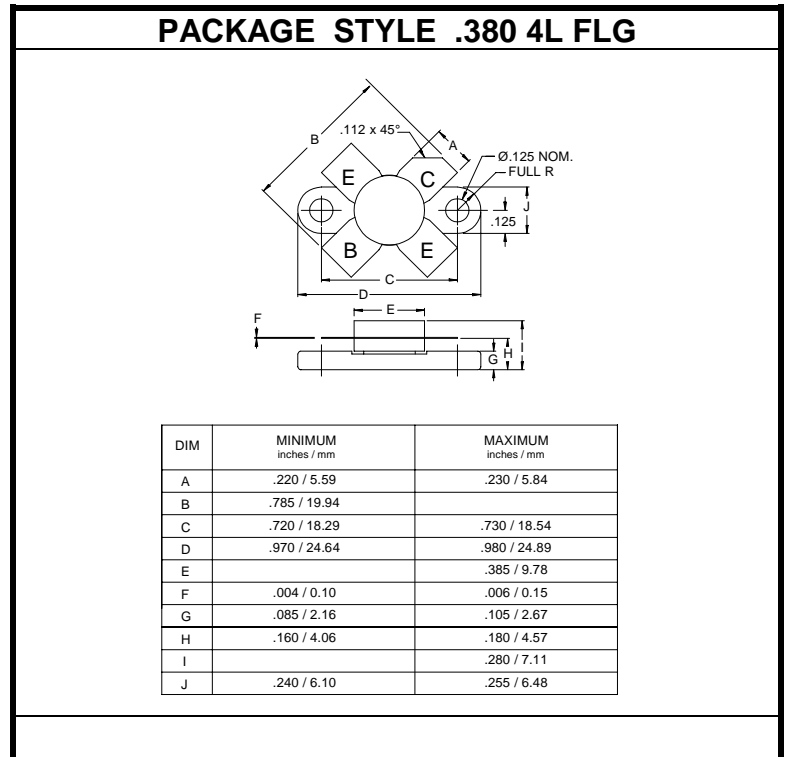
The **ASI BLV20** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

**FEATURES:**

- Common Emitter
- $P_G = 12$  dB at 8.0 W/175 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CB0}$	65 V
$V_{CEO}$	35 V
$V_{CES}$	65 V
$V_{EBO}$	4.0 V
$P_{DISS}$	20 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150°C
$\theta_{JC}$	8.75 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CB0}$	$I_C = 200$ mA	65			V
$BV_{CES}$	$I_C = 2.0$ mA	65			V
$BV_{CEO}$	$I_C = 10$ mA	35			V
$BV_{EBO}$	$I_E = 1.0$ mA	4.0			V
$I_{CB0}$	$V_{CB} = 36$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 400$ mA	10		100	---
$C_C$	$V_{CB} = 28$ V $f = 1.0$ MHz		10		pF
$P_G$ $\eta_c$	$V_{CC} = 28$ V $P_{OUT} = 8.0$ W $f = 175$ MHz	12	60		dB %